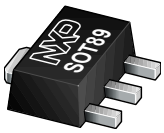


PBHV8115X

150 V, 1 A NPN high-voltage low VCEsat (BISS) transistor

9 December 2013 **Product data sheet**

1. General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9115X.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified
- Medium power SMD plastic package

3. Applications

- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

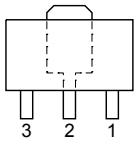
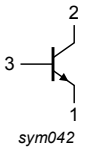
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	150	V
I_C	collector current			-	-	1	A
h_{FE}	DC current gain	V_{CE} = 10 V; I_C = 50 mA; T_{amb} = 25 °C		100	250	-	

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 SOT89	
2	C	collector		
3	B	base		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBHV8115X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PBHV8115X	%4F

[1] % = placeholder for manufacturing site code

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8. Limiting values

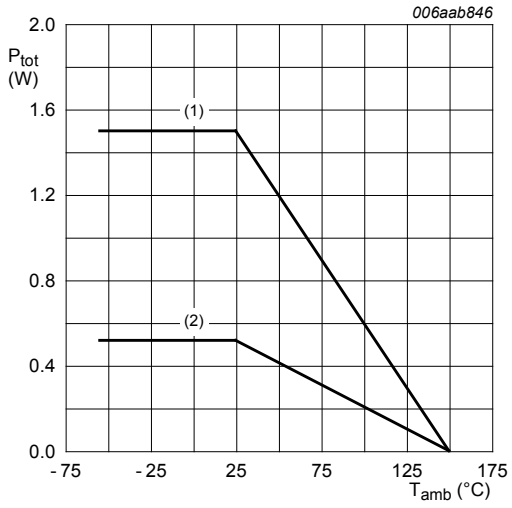
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	400	V
V_{CEO}	collector-emitter voltage	open base		-	150	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
I_C	collector current			-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	2	A
I_{BM}	peak base current			-	400	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	0.52	W
			[2]	-	1.5	W
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm^2.



(1) FR4 PCB, mounting pad for collector 6 cm^2

(2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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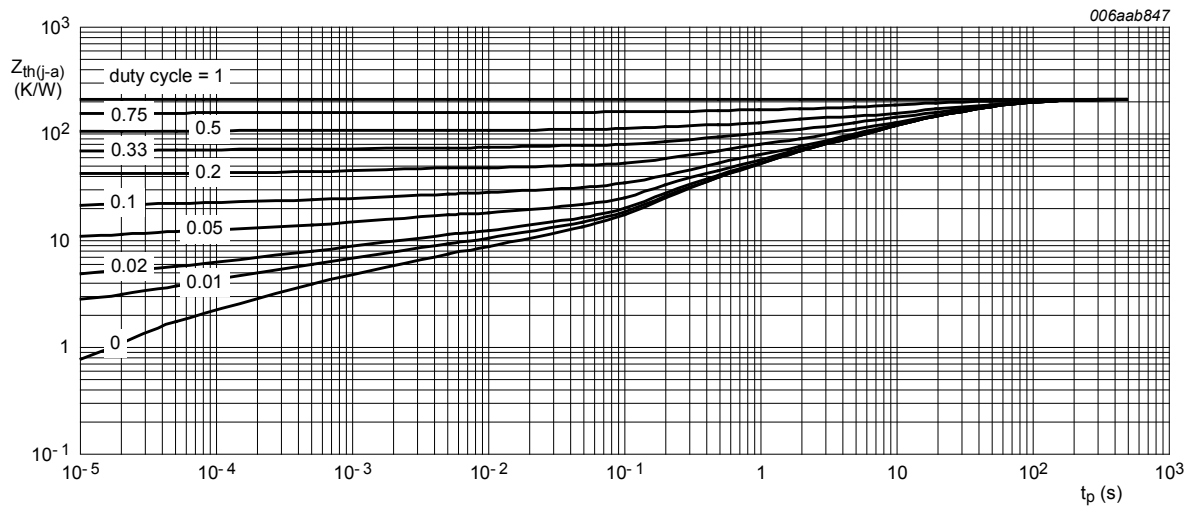
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	240	K/W
			[2]	-	-	83	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	20	K/W

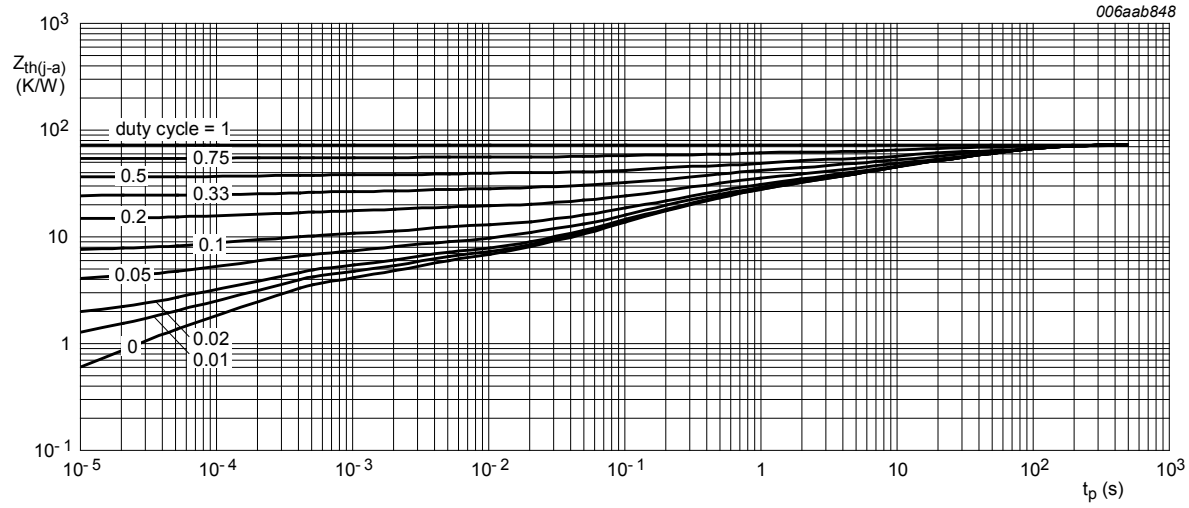
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm^2.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm^2

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = 120 V; I_E = 0 A; T_{amb} = 25 °C		-	-	100	nA
		V_{CB} = 120 V; I_E = 0 A; T_j = 150 °C		-	-	10	µA
I_{CES}	collector-emitter cut-off current	V_{CE} = 120 V; V_{BE} = 0 V; T_{amb} = 25 °C		-	-	100	nA
I_{EBO}	emitter-base cut-off current	V_{EB} = 4 V; I_C = 0 A; T_{amb} = 25 °C		-	-	100	nA
h_{FE}	DC current gain	V_{CE} = 10 V; I_C = 50 mA; T_{amb} = 25 °C		100	250	-	
		V_{CE} = 10 V; I_C = 100 mA; pulsed; $t_p \leq 300$ µs; $\delta \leq 0.02$; T_{amb} = 25 °C		100	250	-	
		V_{CE} = 10 V; I_C = 0.5 A; pulsed; $t_p \leq 300$ µs; $\delta \leq 0.02$; T_{amb} = 25 °C		50	160	-	
		V_{CE} = 10 V; I_C = 1 A; $t_p \leq 300$ µs; $\delta \leq 0.02$; T_{amb} = 25 °C		10	30	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = 100 mA; I_B = 20 mA; T_{amb} = 25 °C		-	33	50	mV
		I_C = 100 mA; I_B = 10 mA; T_{amb} = 25 °C		-	40	60	mV
		I_C = 1 A; I_B = 0.2 A; pulsed; $t_p \leq 300$ µs; $\delta \leq 0.02$; T_{amb} = 25 °C		-	225	350	mV
V_{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 200 mA; pulsed; $t_p \leq 300$ µs; $\delta \leq 0.02$; T_{amb} = 25 °C		-	1.1	1.2	V
t_d	delay time	V_{CC} = 6 V; I_C = 0.5 A; I_{Bon} = 0.1 A; I_{Boff} = -0.1 A; T_{amb} = 25 °C		-	7	-	ns
t_r	rise time			-	565	-	ns
t_{on}	turn-on time			-	572	-	ns
t_s	storage time			-	1530	-	ns
t_f	fall time			-	700	-	ns
t_{off}	turn-off time			-	2230	-	ns
f_T	transition frequency	V_{CE} = 10 V; I_C = 10 mA; f = 100 MHz; T_{amb} = 25 °C		-	30	-	MHz
C_c	collector capacitance	V_{CB} = 20 V; I_E = 0 A; i_e = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	5.7	-	pF
C_e	emitter capacitance	V_{EB} = 0.5 V; I_C = 0 A; i_c = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	150	-	pF

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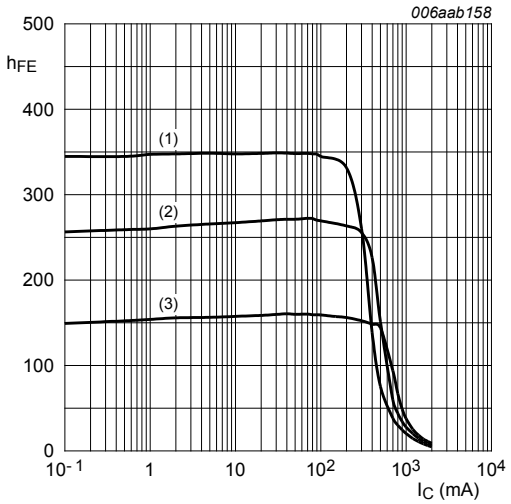


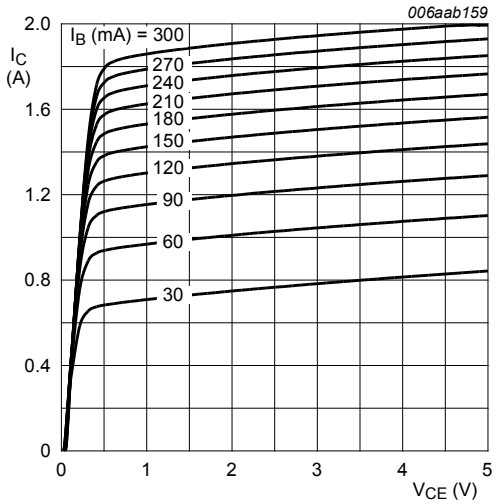
V_{CE} = 10 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

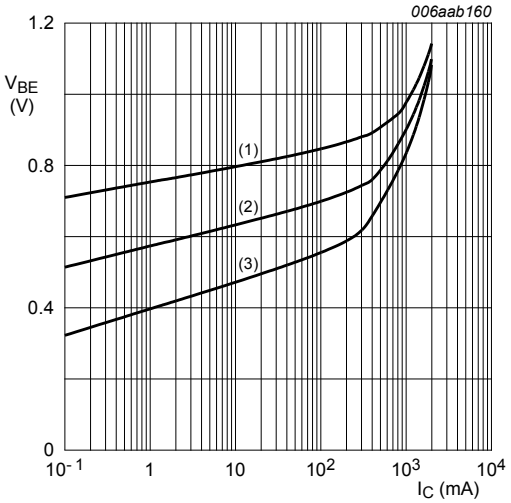
(3) T_{amb} = -55 °C

Fig. 4. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 5. Collector current as a function of collector-emitter voltage; typical values



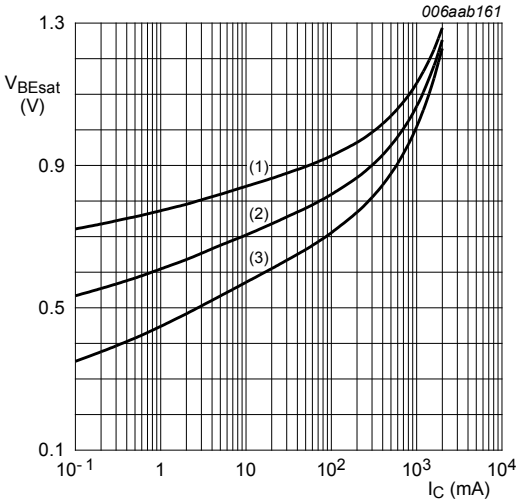
V_{CE} = 10 V

(1) T_{amb} = -55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



I_C/I_B = 5

(1) T_{amb} = -55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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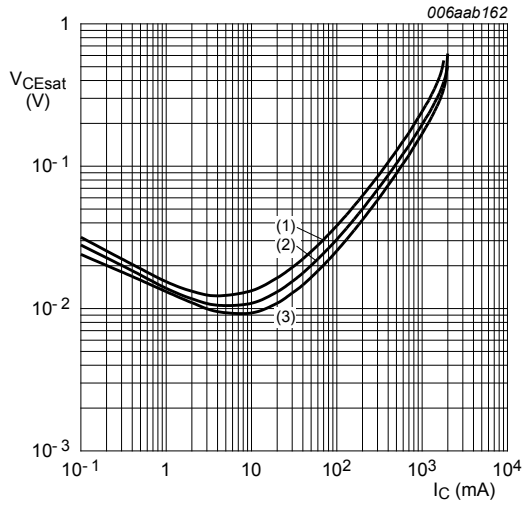
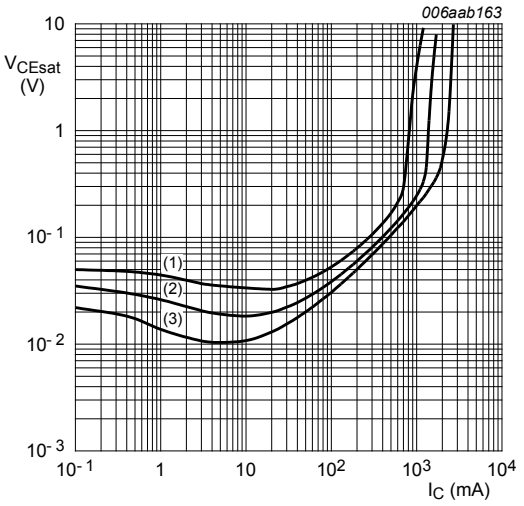


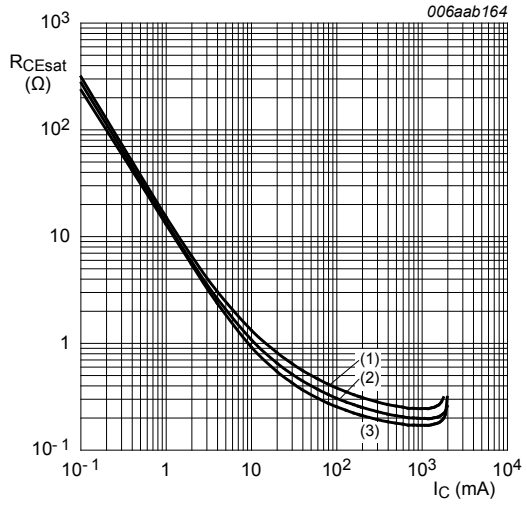
I_C/I_B = 5
(1) T_{amb} = 100 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



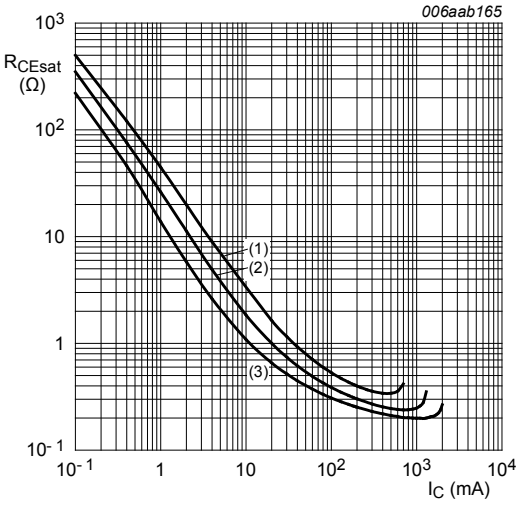
T_{amb} = 25 °C
(1) I_C/I_B = 20
(2) I_C/I_B = 10
(3) I_C/I_B = 5

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



I_C/I_B = 5
(1) T_{amb} = 100 °C
(2) T_{amb} = 25 °C
(3) T_{amb} = -55 °C

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



T_{amb} = 25 °C
(1) I_C/I_B = 20
(2) I_C/I_B = 10
(3) I_C/I_B = 5

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

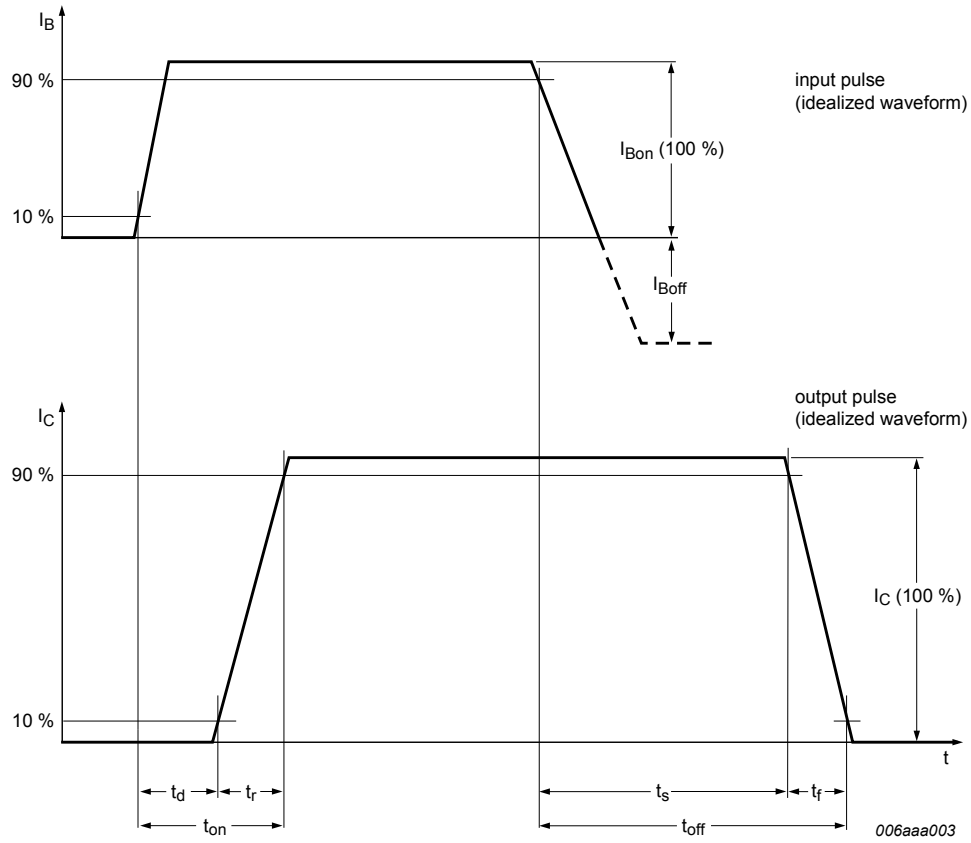

Fig. 12. BISS transistor switching time definition

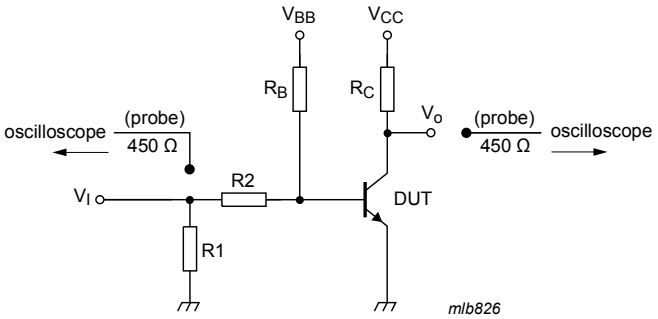

Fig. 13. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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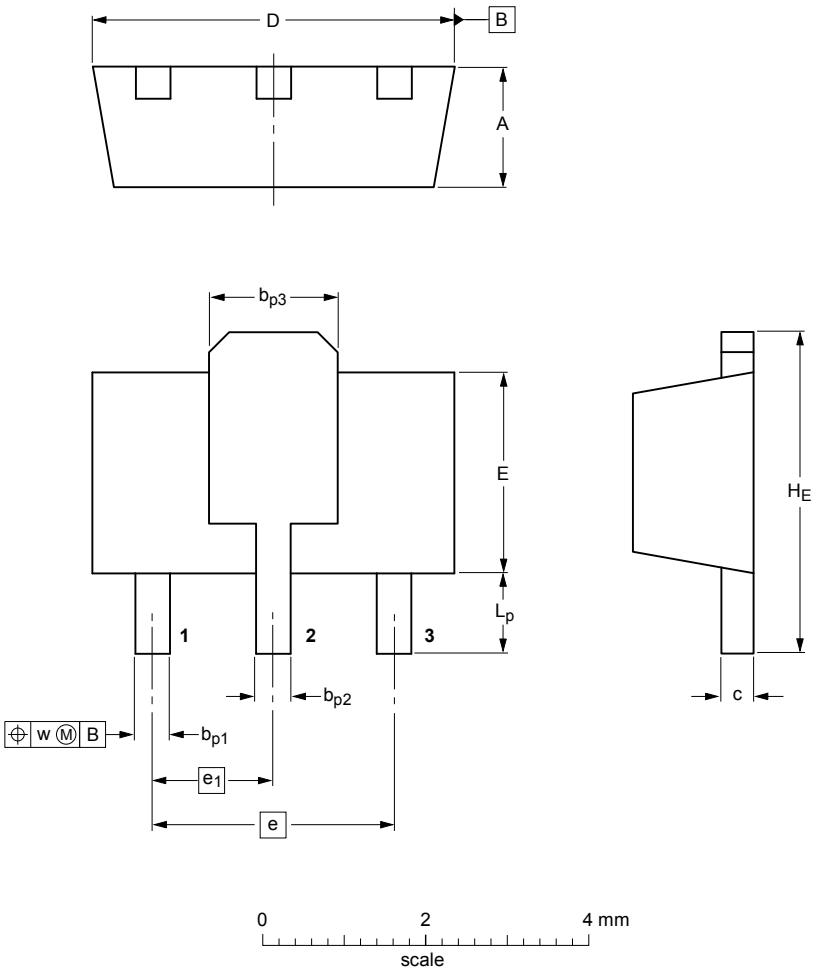
12. Package outline

Plastic surface-mounted package; exposed die pad for good heat transfer; 3 leads **SOT89**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT89		TO-243	SC-62			~~06-03-16~~ 06-08-29

Fig. 14. Package outline SOT89

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13. Soldering

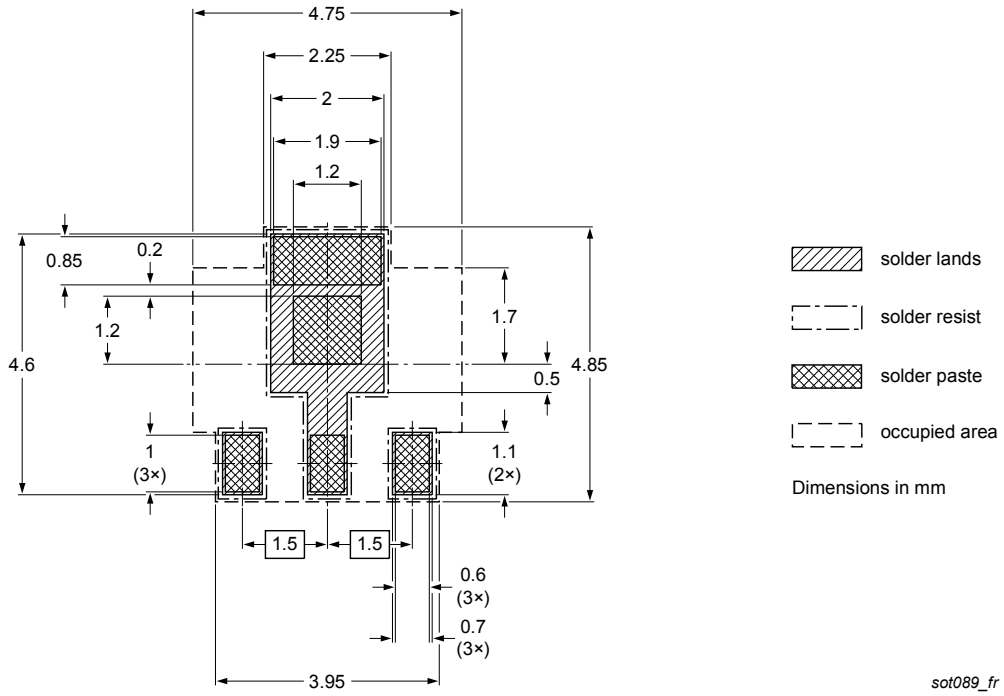

Fig. 15. Reflow soldering footprint for SOT89

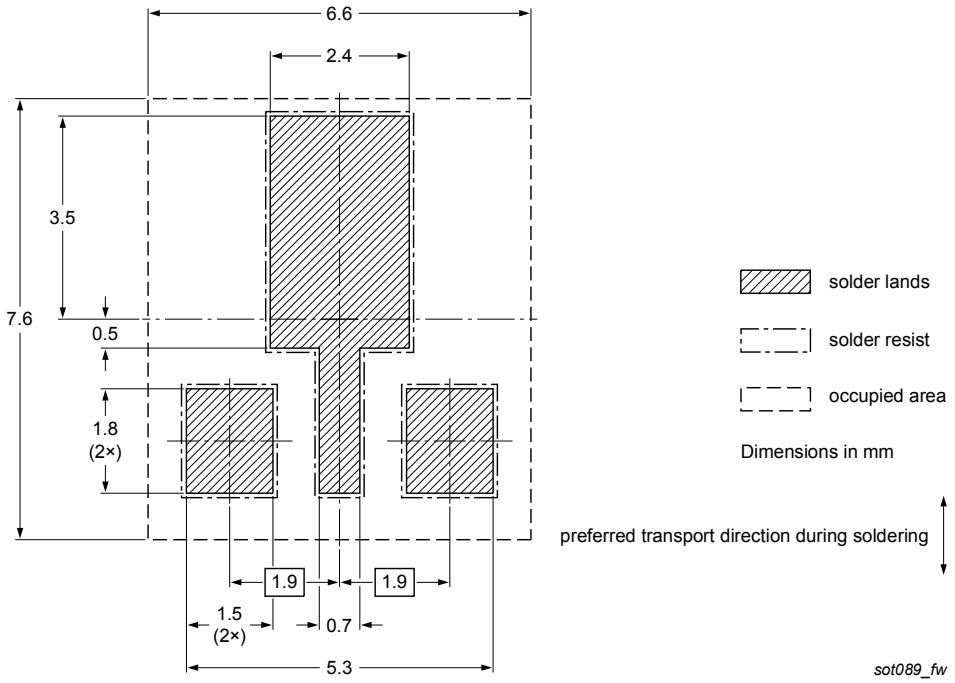

Fig. 16. Wave soldering footprint for SOT89

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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8115X v.1	20131209	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Date of release: 9 December 2013